

N-channel TrenchMOS standard level FET Rev. 03 — 7 April 2010

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using NXP High-Performance Automotive (HPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V Loads
- Automotive systems

- General purpose power switch
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

	Quick reference du						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 4</u>	[1]	-	-	75	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	105	W
Static cha	racteristics						
R _{DSon}	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 25 \text{ °C}; \text{ see } \underline{\text{Figure 12}}; \\ \text{see } \underline{\text{Figure 13}} \end{array}$		-	5	7	mΩ
Avalanche	e ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 75 \text{ A}; \text{V}_{sup} \leq 30 \text{V}; \\ R_{GS} &= 50 \Omega; \text{V}_{GS} = 10 \text{V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{unclamped} \end{split} $		-	-	198	mJ
Dynamic o	characteristics						
Q_{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V};$ $V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure } 14}{14}$		-	10.7	-	nC

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[1] Continuous current is limited by package.

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	mbb076 S
			SOT669 (LFPAK)	

3. Ordering information

Table 3. Ord	lering information		
Type number	Package		
	Name	Description	Version
BUK7Y07-30B	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _i ≥ 25 °C; T _i ≤ 175 °C		-	-	30	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	30	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 4</u>	<u>[1]</u>	-	-	75	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1		-	-	63	А
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \ \mu$ s; pulsed; see <u>Figure 4</u>		-	-	356	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	105	W
T _{stg}	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-drai	n diode						
ls	source current	T _{mb} = 25 °C	[1]	-	-	75	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	356	А
Avalanche r	uggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$\label{eq:ld} \begin{array}{l} I_D = 75 \text{ A}; \ V_{sup} \leq 30 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped \end{array}$		-	-	198	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy	see Figure 3	[2][3][4] [5]	-	-	-	J

[1] Continuous current is limited by package.

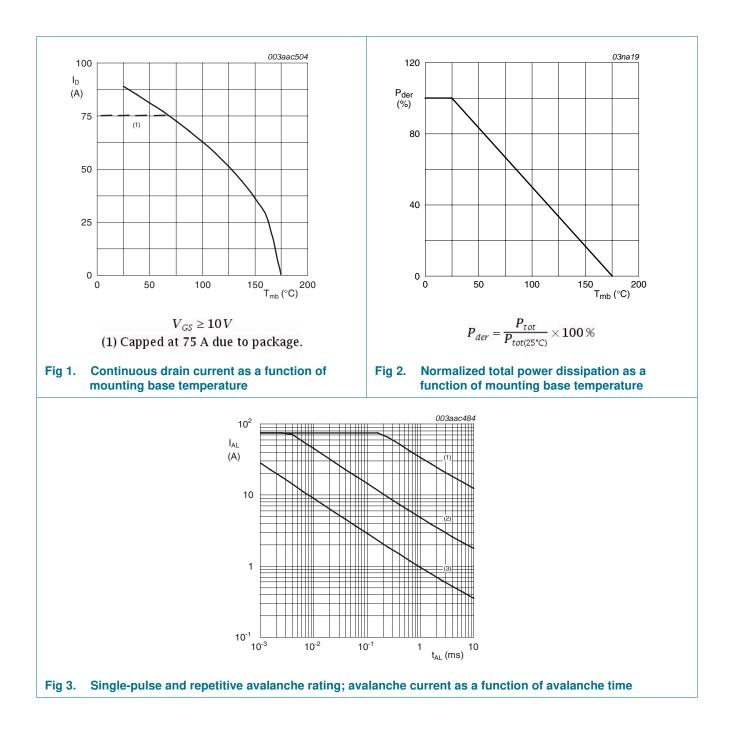
[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[4] Refer to application note AN10273 for further information.

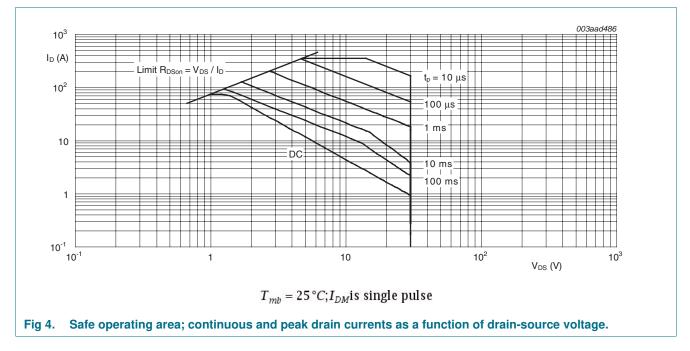
[5] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.

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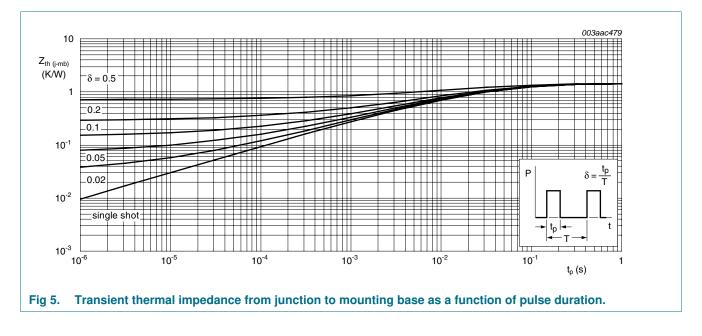
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Thermal characteristics 5.

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 5</u>	-	-	1.42	K/W



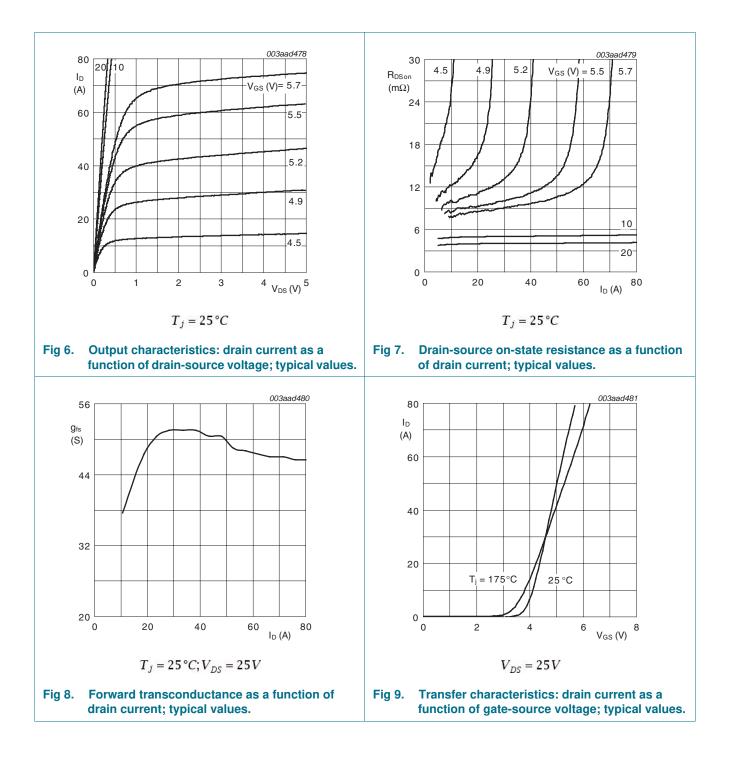
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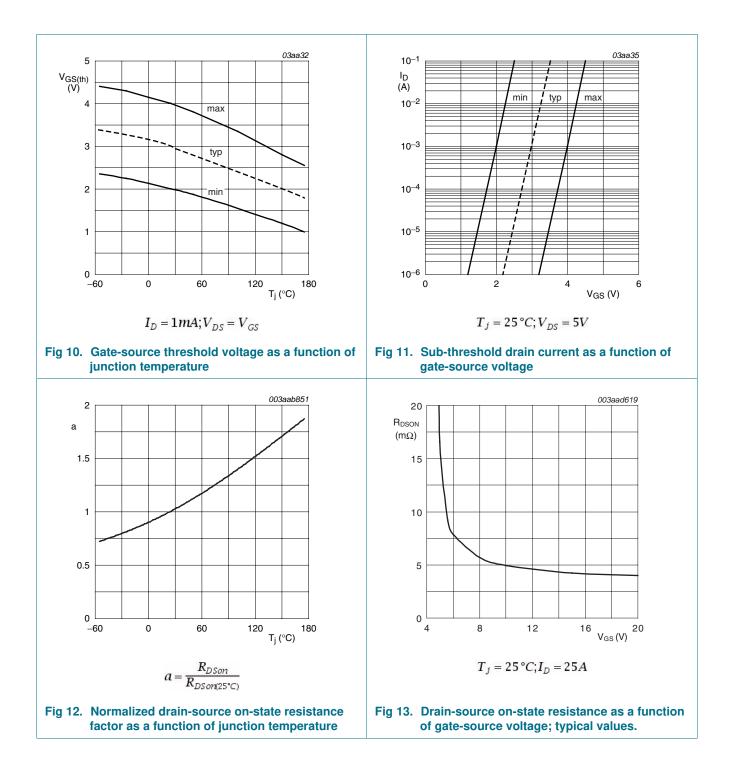
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	30	-	-	V
	breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	1	-	-	V
IDSS	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	$V_{DS} = 0 V; V_{GS} = 20 V; T_j = 25 °C$	-	2	100	nA
		$V_{DS} = 0 V; V_{GS} = -20 V; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	13.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	5	7	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$	-	31	-	nC
Q _{GS}	gate-source charge	see Figure 14	-	9.5	-	nC
Q _{GD}	gate-drain charge		-	10.7	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1330	1773	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 15</u>	-	495	594	pF
C _{rss}	reverse transfer capacitance		-	206	282	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 25 \text{ V}; \text{ R}_{L} = 1 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	17	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega$	-	30	-	ns
t _{d(off)}	turn-off delay time		-	40	-	ns
t _f	fall time		-	28	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{V}; \text{T}_j = 25 ^{\circ}\text{C}; \\ \text{see } \underline{\text{Figure 16}}$	-	0.85	1.2	V
rr	reverse recovery time	$I_{S} = 20 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu s; V_{GS} = 0 \text{ V};$	-	39	-	ns
Q _r	recovered charge	$V_{DS} = 25 V$	-	53	-	nC

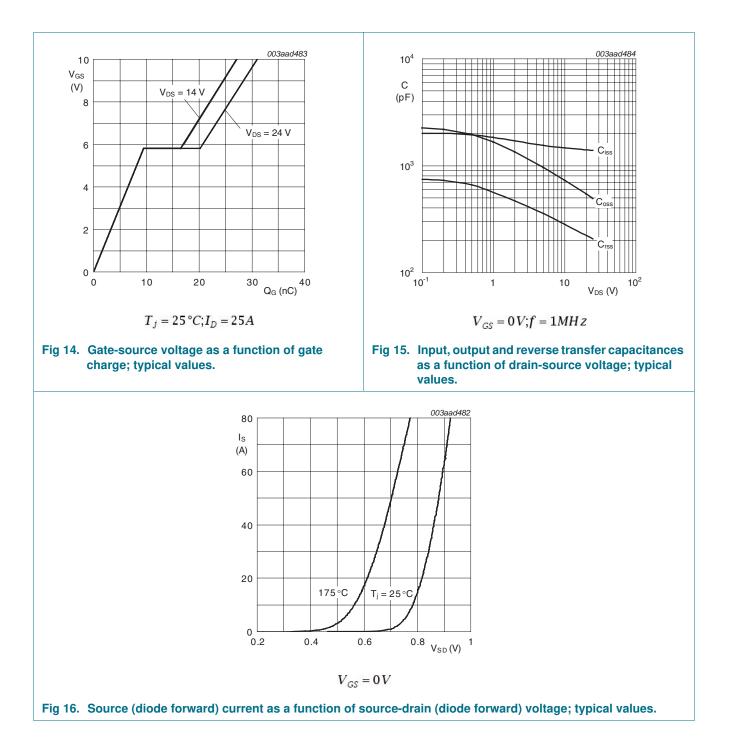
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7. Package outline

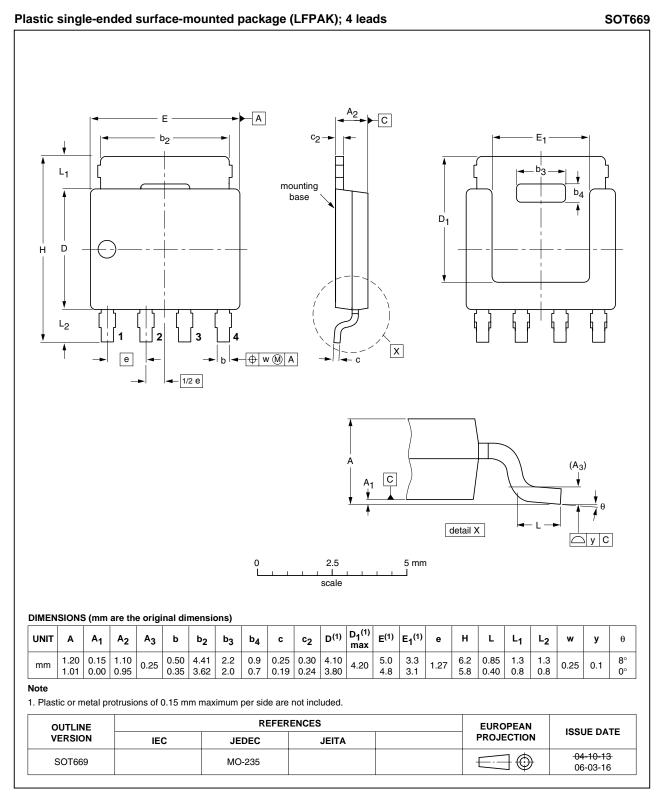


Fig 17. Package outline SOT669 (LFPAK)

BUK7Y07-30B Product data sheet

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8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7Y07-30B_3	20100407	Product data sheet	-	BUK7Y07-30B_2
Modifications:	 Status cha 	nged from objective to pro	duct.	
BUK7Y07-30B_2	20100215	Objective data sheet	-	BUK7Y07-30B_1

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia.com</u>.

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